# MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

# **AOD403**

**Product specification** 





## **General Features**

- -30 V,-70A, RDS(ON) =5.5mΩ@VGS = 10V
- Fast switching
- Green Device Available

# **Application**

- MB / VGA / Vcore
- POL Applications
- Load Switch
- LED Applicatio

## **Reference News**

PACKAGE OUTLINE	Pin Configuration	Marking
J. State of the st	G	MSKSEMI AOD403
TO-252	ŝ	



## **Absolute Maximum Ratings** Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-30	V
VGS	Gate-Source Voltage	±20	V
ID	Drain Current – Continuous (TC=25C)	-70	А
ID	Drain Current – Continuous (T <sub>C</sub> =100C)	-44	А
IDM	Drain Current – Pulsed <sup>1</sup>	-280	А
PD	Power Dissipation (TC=25C)	73.5	W
PU	Power Dissipation – Derate above 25C	0.58	W/ C
TSTG	Storage Temperature Range	-55 to 150	С
TJ	Operating Junction Temperature Range	-55 to 150	С

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient	<u>.</u> 	62	c/ W
Reuc	Thermal Resistance Junction to Case		1.7	C/ W

## Electrical Characteristics (TJ=25 ℃, unless otherwise noted)

## **Off** Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V , $I_D$ =-250uA	-30			<b>&gt;</b>
△BV <sub>DSS</sub> /△T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 250 , I <sub>D</sub> =-1mA		-0.03		V/ C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-30V , V <sub>GS</sub> =0V , T <sub>J</sub> =250			<sub>-</sub> 1	uA
1033		V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V , T <sub>J</sub> =1250			-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA



#### On **Characteristics**

		V <sub>GS</sub> =-10V , I <sub>D</sub> =-10A		5.5	8.0	mΩ	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-8A					
				7.5	10	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage		-1.0	-1.6	-2.5	V	
	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=-250uA$					
$\triangle V_{GS(th)}$				4		mV/ C	
gfs	Forward Transconductance	V <sub>DS</sub> =-10V , I <sub>D</sub> =-10A		14		S	

vitching Characteristics

Dynamic	and switching	Characteristics				
Qg	Total Gate Charge <sup>2, 3</sup>			35		
Q <sub>gs</sub>	Gate-Source Charge <sup>2, 3</sup>	V <sub>DS</sub> =-15V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-10A		10.8		nC
$Q_{qd}$	Gate-Drain Charge <sup>2, 3</sup>			10.6		
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2, 3</sup>			24.5		
Tr	Rise Time <sup>2,3</sup>	$V_{DD}$ =-15V , $V_{GS}$ =-10V , $R_G$ =6 $\Omega$		10.5	-	ns
$T_{d(off)}$	Turn-Off Delay Time <sup>2, 3</sup>	I <sub>D</sub> =-1A	· 	156.8		
T <sub>f</sub>	Fall Time <sup>2,3</sup>			50		
Ciss	Input Capacitance			3300		
Coss	Output Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , F=1MHz		410		pF
Crss	Reverse Transfer Capacitar	се		280		
Rg	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz		8.5		Ω

#### Drain- Source Diode Characteristics and Maximum **Ratings**

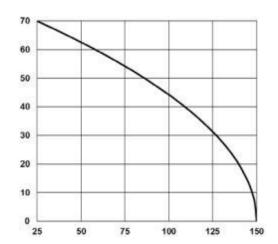
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-70	Α
I <sub>SM</sub>	Pulsed Source Current	vg-vb-ov , r orce current			-140	Α
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =250			- 1.2	V

### Note:

- 1 . Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width  $\leq$  300 us , duty cycle  $\leq$  2% .
- 3. Essentially independent of operating temperature.



-ID , Continuous Drain Current



TJ ,JunctionTemperature(°C)

Fig. 1 Continuous Drain Current vs. TC

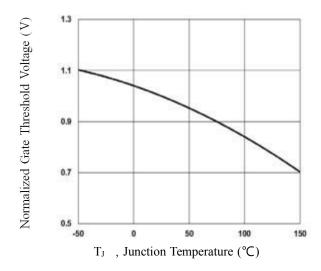
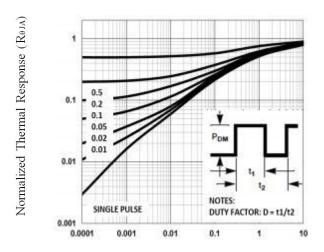
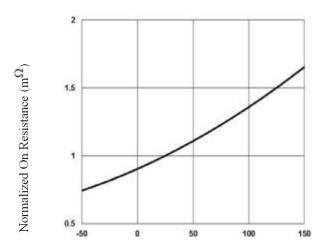


Fig. 3 Normalized Vth vs. TJ



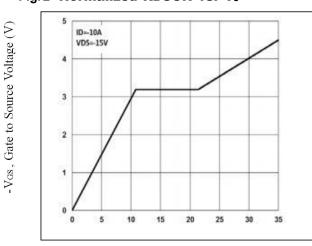
Square Wave Pulse Duration (s)

Fig. 5 Normalized Transient Response



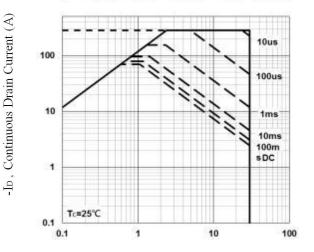
TJ, Juction Temperature(°C)

Fig. 2 Normalized RDSON vs. TJ



Qg, Gate Charge (nC)

Fig. 4 Gate Charge Waveform

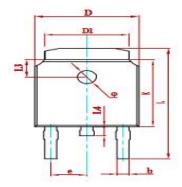


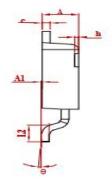
V<sub>DS</sub> , Drain to Source Voltage(v)

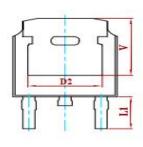
Fig. 6 Maximum Safe Operation Area



## PACKAGE MECHANICAL DATA

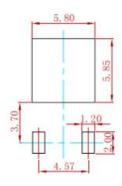






Symbol	Dimensions	In Millimeters	Dimensions	In Inches
Syllibol	Min.	Max.	Min.	Max.
Α	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
С	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830	REF.	0.190	REF.
E	6.000	6.200	0.236	0.244
е	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900	REF.	0.114	REF.
L2	1.400	1.700	0.055	0.067
L3	1.600	REF.	0.063	REF.
L4	0.600	1.000	0.024	0.039
Ф	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250	REF.	0.207	REF.

# **Suggested Pad Layout**



#### Note:

- 1 Controlling dimension in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only,

## **REEL SPECIFICATION**

P/N	PKG	QTY
AOD403	TO-252	2500



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